# BCW66GLT1G, SBCW66GLT1G

# **General Purpose Transistor**

## **NPN Silicon**

#### **Features**

- AEC-Q101 Qualified and PPAP Capable
- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant\*



Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V <sub>CEO</sub>	45	Vdc
Collector - Base Voltage	V <sub>CBO</sub>	75	Vdc
Emitter – Base Voltage	V <sub>EBO</sub>	5.0	Vdc
Collector Current – Continuous	Ic	800	mAdc
Collector Current – Pulsed	Ic	1200	mAdc

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

## THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1), T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{ heta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	300 2.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{ heta JA}$	417	°C/W
Junction and Storage Temperature	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

- 1. FR-5 =  $1.0 \times 0.75 \times 0.062$  in.
- 2. Alumina =  $0.4 \times 0.3 \times 0.024$  in 99.5% alumina.

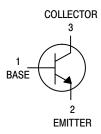


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SOT-23 (TO-236) CASE 318-08 STYLE 6



## **MARKING DIAGRAM**



EG = Specific Device Code

M = Date Code\*

= Pb-Free Package

(\*Note: Microdot may be in either location)

\*Date Code orientation and/or overbar may vary depending upon manufacturing location.

## **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
BCW66GLT1G	SOT-23 (Pb-Free)	3,000/Tape & Reel
SBCW66GLT1G	SOT-23 (Pb-Free)	3,000/Tape & Reel
BCW66GLT3G	SOT-23 (Pb-Free)	10,000/Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

## BCW66GLT1G, SBCW66GLT1G

## **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS	•				
Collector – Emitter Breakdown Voltage (I <sub>C</sub> = 10 mAdc, I <sub>B</sub> = 0)	V <sub>(BR)CEO</sub>	45	-	-	Vdc
Collector – Emitter Breakdown Voltage (I <sub>C</sub> = 10 μAdc, V <sub>EB</sub> = 0)	V <sub>(BR)CES</sub>	75	_	_	Vdc
Emitter – Base Breakdown Voltage ( $I_E = 10 \mu Adc, I_C = 0$ )	V <sub>(BR)EBO</sub>	5.0	-	-	Vdc
Collector Cutoff Current $(V_{CE} = 45 \text{ Vdc}, I_E = 0)$ $(V_{CE} = 45 \text{ Vdc}, I_E = 0, T_A = 150^{\circ}\text{C})$	I <sub>CES</sub>	- -	- -	20 20	nAdc μAdc
Emitter Cutoff Current (V <sub>EB</sub> = 4.0 Vdc, I <sub>C</sub> = 0)	I <sub>EBO</sub>	_	_	20	nAdc
ON CHARACTERISTICS	•				
DC Current Gain $ \begin{aligned} &(I_C=100~\mu\text{Adc},~V_{CE}=10~\text{Vdc})\\ &(I_C=10~\text{mAdc},~V_{CE}=1.0~\text{Vdc})\\ &(I_C=100~\text{mAdc},~V_{CE}=1.0~\text{Vdc})\\ &(I_C=500~\text{mAdc},~V_{CE}=2.0~\text{Vdc}) \end{aligned} $	h <sub>FE</sub>	50 110 160 60		- - 400 -	-
Collector – Emitter Saturation Voltage (I <sub>C</sub> = 500 mAdc, I <sub>B</sub> = 50 mAdc) (I <sub>C</sub> = 100 mAdc, I <sub>B</sub> = 10 mAdc)	V <sub>CE(sat)</sub>	_ _	_ _	0.7 0.3	Vdc
Base – Emitter Saturation Voltage (I <sub>C</sub> = 500 mAdc, I <sub>B</sub> = 50 mAdc)	V <sub>BE(sat)</sub>	_	-	2.0	Vdc
SMALL-SIGNAL CHARACTERISTICS	•				
Current - Gain — Bandwidth Product (I <sub>C</sub> = 20 mAdc, V <sub>CE</sub> = 10 Vdc, f = 100 MHz)	f <sub>T</sub>	100	-	-	MHz
Output Capacitance (V <sub>CB</sub> = 10 Vdc, I <sub>E</sub> = 0, f = 1.0 MHz)	C <sub>obo</sub>	-	-	12	pF
Input Capacitance (V <sub>EB</sub> = 0.5 Vdc, I <sub>C</sub> = 0, f = 1.0 MHz)	C <sub>ibo</sub>	_	-	80	pF
Noise Figure (V <sub>CE</sub> = 5.0 Vdc, I <sub>C</sub> = 0.2 mAdc, R <sub>S</sub> = 1.0 k $\Omega$ , f = 1.0 kHz, BW = 200 Hz)	NF	-	-	10	dB
SWITCHING CHARACTERISTICS	•		•	•	
Turn-On Time (I <sub>B1</sub> = I <sub>B2</sub> = 15 mAdc)	t <sub>on</sub>	_	_	100	ns
Turn–Off Time ( $I_C$ = 150 mAdc, $R_L$ = 150 $\Omega$ )	t <sub>off</sub>	_	_	400	ns

## **TYPICAL CHARACTERISTICS**

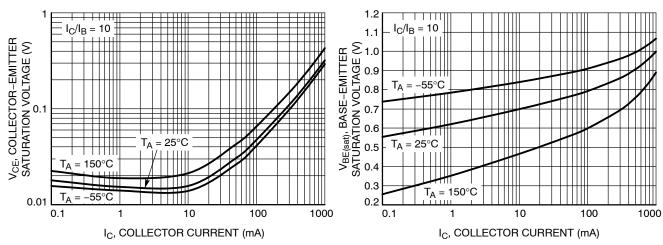


Figure 1. Collector Emitter Saturation Voltage vs. Collector Current

Figure 2. Base Emitter Saturation Voltage vs.
Collector Current

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## **TYPICAL CHARACTERISTICS**

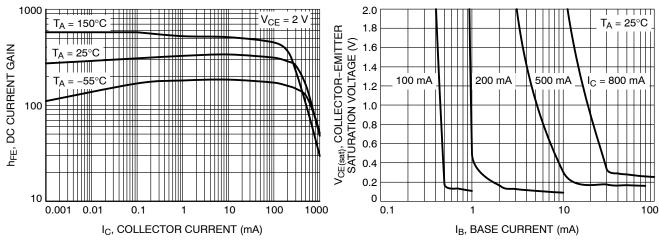


Figure 3. DC Current Gain vs. Collector Current

Figure 4. Saturation Region

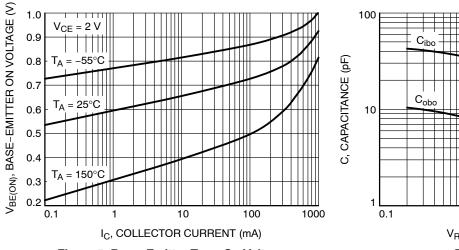


Figure 5. Base-Emitter Turn-On Voltage vs. Collector Current

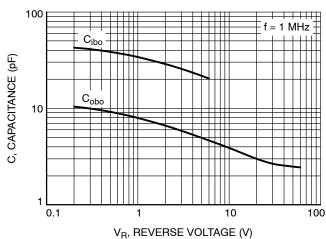


Figure 6. Capacitance

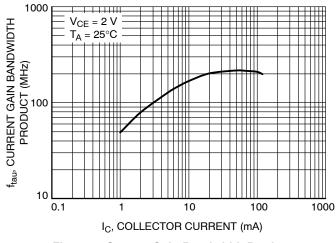


Figure 7. Current Gain Bandwidth Product vs.

Collector Current

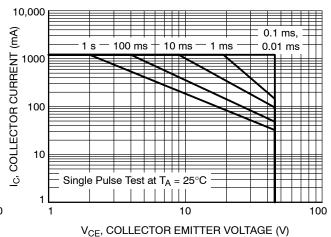
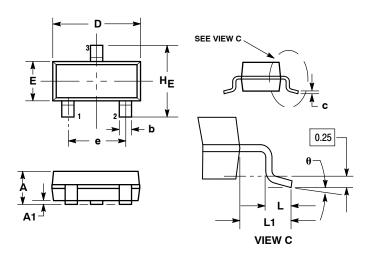


Figure 8. Safe Operating Area

## BCW66GLT1G, SBCW66GLT1G

## PACKAGE DIMENSIONS

SOT-23 (TO-236) CASE 318-08 **ISSUE AP** 



#### NOTES

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: INCH.
  MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

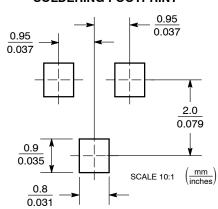
	М	ILLIMETE	RS	INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
С	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.081
L	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
HE	2.10	2.40	2.64	0.083	0.094	0.104
θ	0°		10°	0°		10°

## STYLE 6:

PIN 1. BASE

- **EMITTER** 2.
- COLLECTOR

## **SOLDERING FOOTPRINT**



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